ALPHA & OMEGA SEMICONDUCTOR

AONX38168A

25V Dual Asymmetric N-Channel XSPairFET

General Description

- Trench Power MOSFET technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- High Current Capability
- RoHS 2.0 and Halogen-Free Compliant

Applications

- DC/DC Converters in PC, Servers
- Point of Load Converters

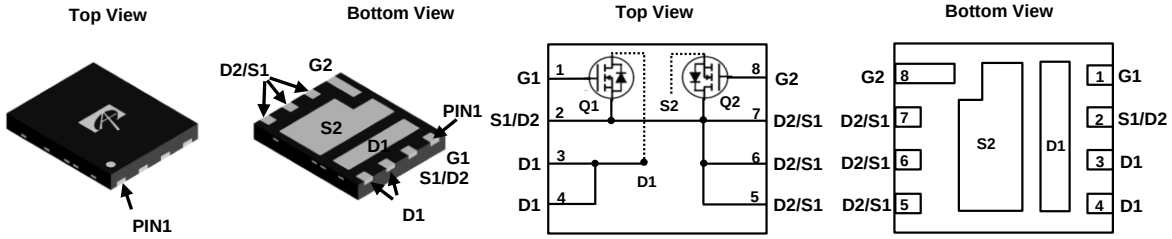
Product Summary

	Q1	Q2
V_{DS}	25V	25V
I_D (at V_{GS}=10V)	87A	226A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 3.6mΩ	< 0.92mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 5mΩ	< 1.2mΩ

100% UIS Tested
100% Rg Tested

GREEN Product

DFN 5X6E



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AONX38168A	DFN 5x6E	Tape & Reel	3000

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Max Q1	Max Q2	Units
Drain-Source Voltage		V_{DS}	25	25	V
Gate-Source Voltage		V_{GS}	±12	±12	V
Continuous Drain Current	T_C=25°C	I_D	87	226	A
	T_C=100°C		54	142	
Pulsed Drain Current [C]		I_{DM}	145	378	
Continuous Drain Current	T_A=25°C	I_{DSM}	24	48	A
	T_A=70°C		20	38	
Avalanche Current [C]		I_{AS}	60	80	A
Avalanche energy	L=0.01mH [C]	E_{AS}	18	32	mJ
Power Dissipation [B]	T_C=25°C	P_D	41	73	W
	T_C=100°C		16	29	
Power Dissipation [A]	T_A=25°C	P_{DSM}	3.1	3.2	W
	T_A=70°C		2	2.1	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150		°C

Thermal Characteristics

Parameter		Symbol	Typ Q1	Typ Q2	Max Q1	Max Q2	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	32	30	40	38	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		60	55	75	68	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	2.4	1.35	3	1.7	°C/W

Q1 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	25			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=25V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	1.3	1.7	2.1	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		2.9	3.6	mΩ
		T_J=125°C		3.8	4.7	
		V_{GS}=4.5V, I_D=20A		3.7	5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		220		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				50	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=12.5V, f=1MHz		1240		pF
C_{oss}	Output Capacitance			460		pF
C_{rss}	Reverse Transfer Capacitance			47		pF
R_g	Gate resistance	f=1MHz	0.65	1.3	1.95	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=12.5V, I_D=20A		16	23	nC
Q_g(4.5V)	Total Gate Charge			7.2	11	nC
Q_{gs}	Gate Source Charge			2.8		nC
Q_{gd}	Gate Drain Charge			2		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=12.5V, R_L=0.625Ω, R_{GEN}=3Ω		6.2		ns
t_r	Turn-On Rise Time			2.6		ns
$t_{D(off)}$	Turn-Off DelayTime			21		ns
t_f	Turn-Off Fall Time			2.8		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs		11.3		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs		18.4		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

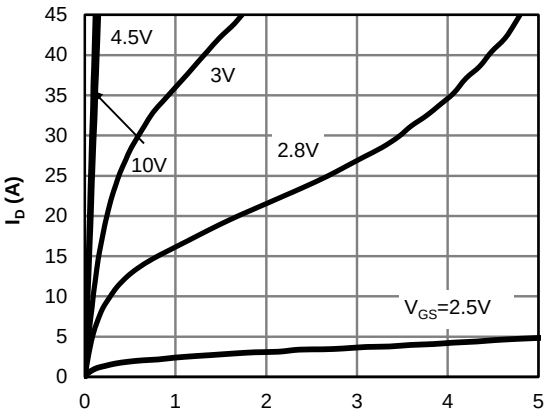


Figure 1: On-Region Characteristics (Note E)

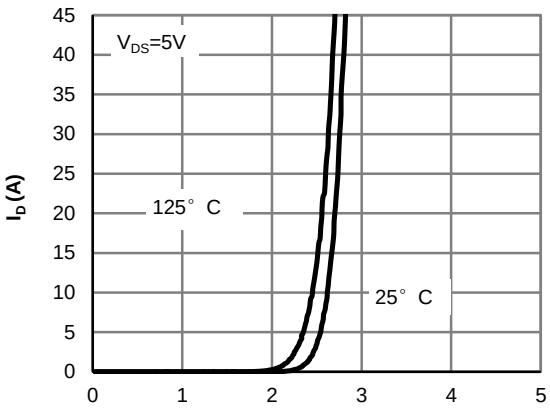


Figure 2: Transfer Characteristics (Note E)

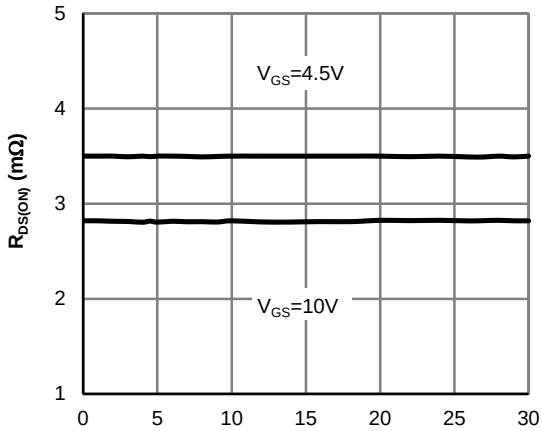


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

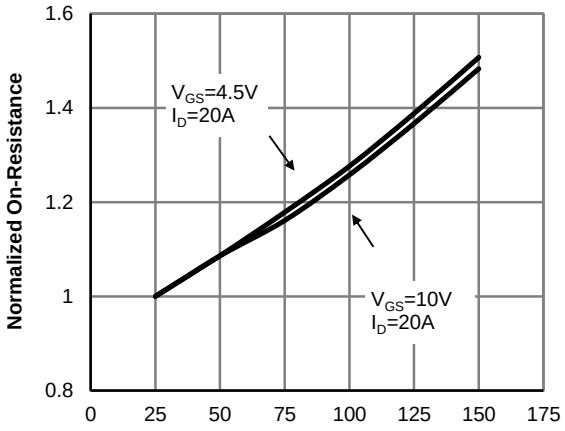


Figure 4: On-Resistance vs. Junction Temperature (Note E)

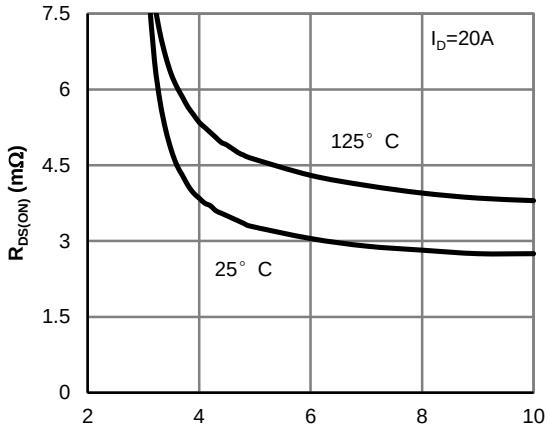


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

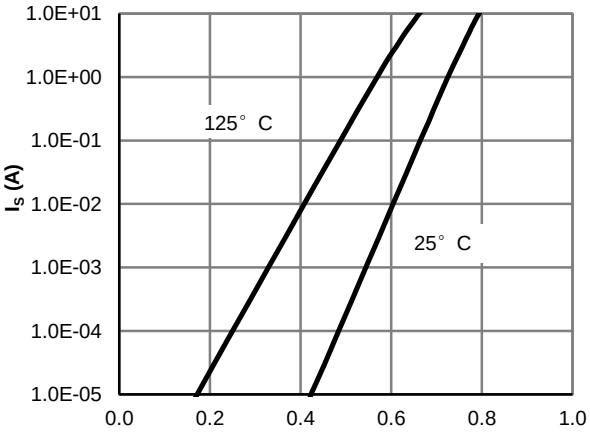


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

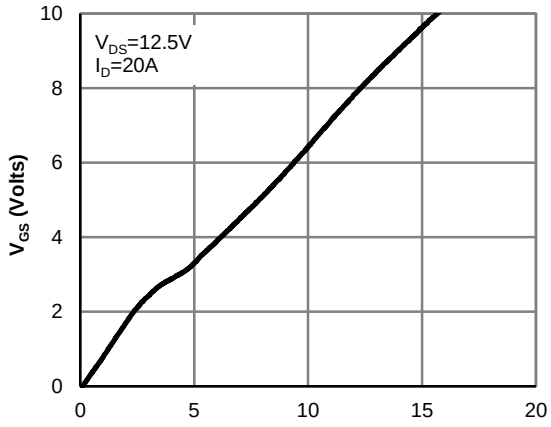


Figure 7: Gate-Charge Characteristics

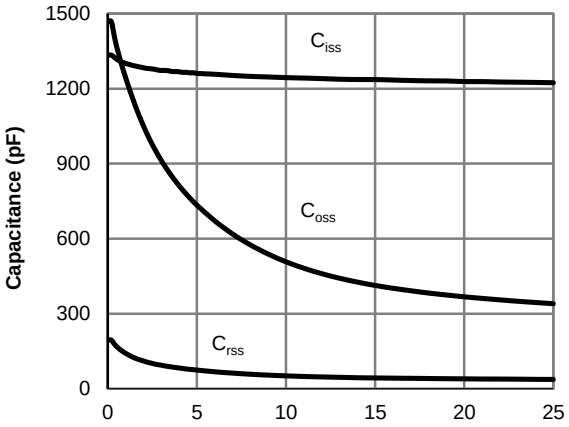


Figure 8: Capacitance Characteristics

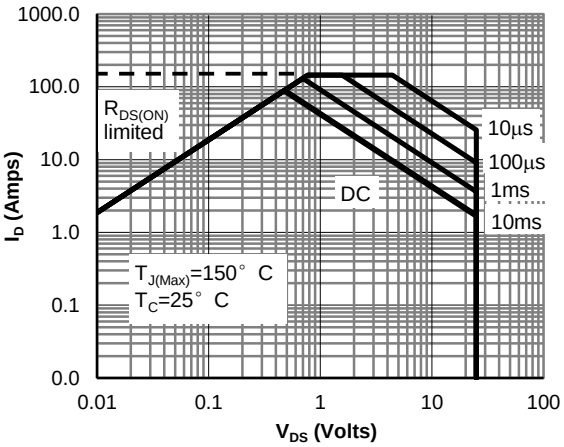


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

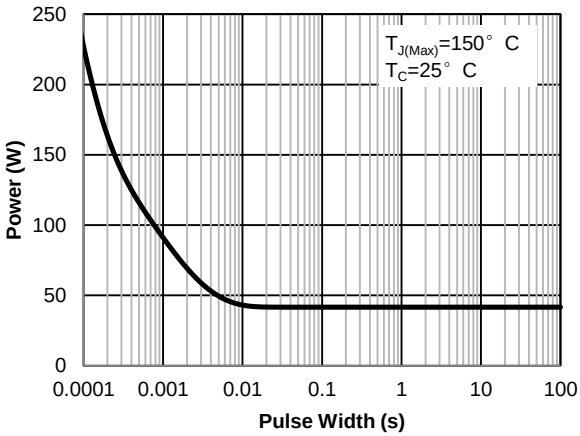


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

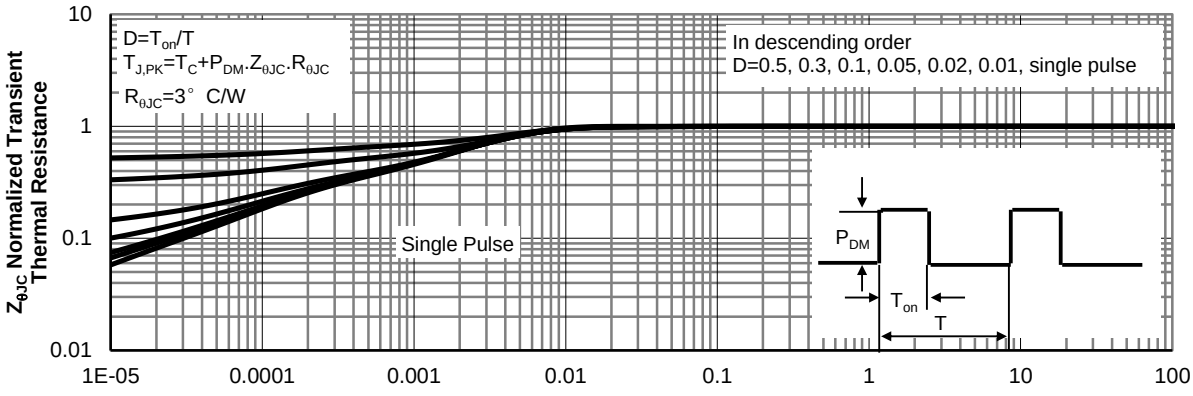


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

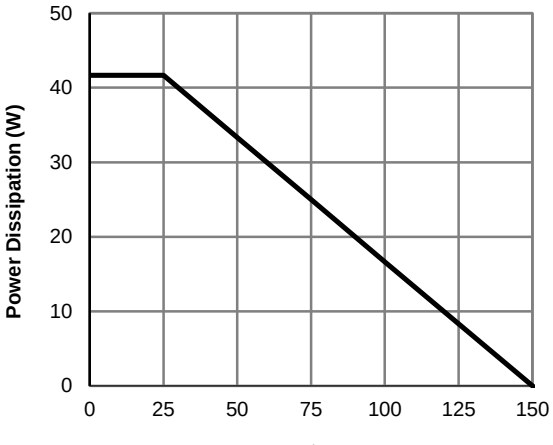


Figure 12: Power De-rating (Note F)

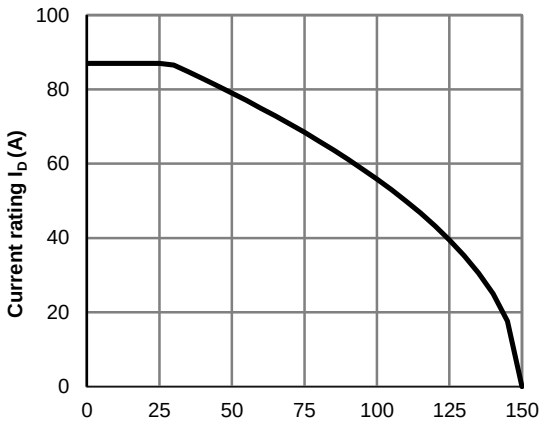


Figure 13: Current De-rating (Note F)

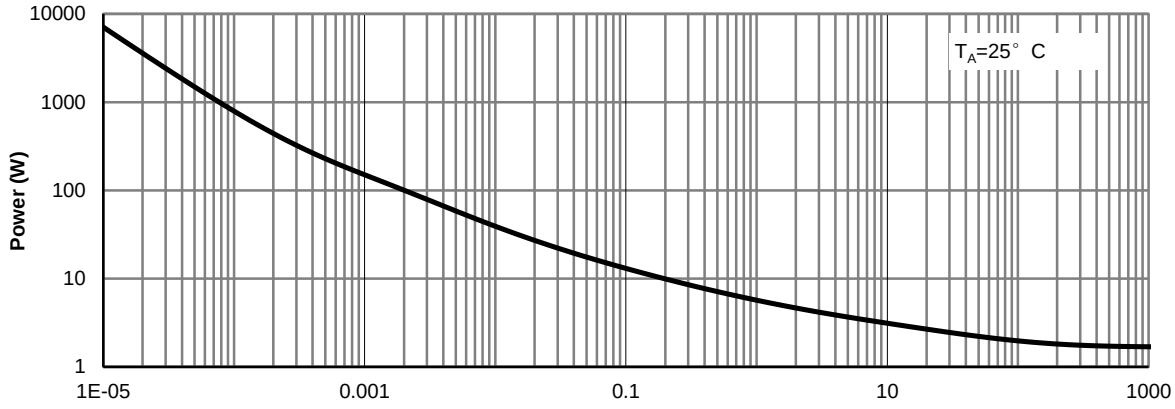


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

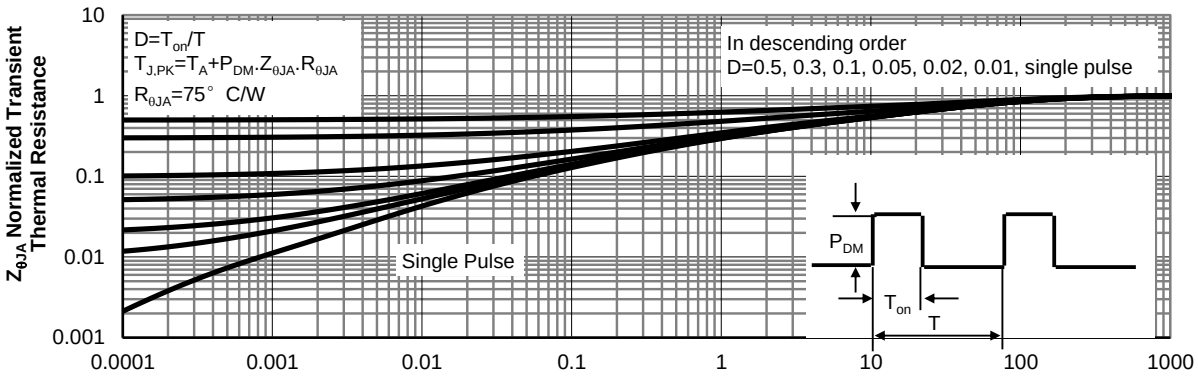


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

Q2 Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	25			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=25V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±12V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	1	1.4	1.8	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		0.75	0.92	mΩ
		T_J=125°C		1.05	1.3	
		V_{GS}=4.5V, I_D=20A		0.95	1.2	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		200		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.67	1	V
I_S	Maximum Body-Diode Continuous Current				90	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=12.5V, f=1MHz		4940		pF
C_{oss}	Output Capacitance			1330		pF
C_{rss}	Reverse Transfer Capacitance			130		pF
R_g	Gate resistance	f=1MHz	0.6	1.2	1.8	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=12.5V, I_D=20A		62	87	nC
Q_g(4.5V)	Total Gate Charge			26	37	nC
Q_{gs}	Gate Source Charge			11.6		nC
Q_{gd}	Gate Drain Charge			4.6		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=12.5V, R_L=0.625Ω, R_{GEN}=3Ω		8.7		ns
t_r	Turn-On Rise Time			3.2		ns
$t_{D(off)}$	Turn-Off DelayTime			56		ns
t_f	Turn-Off Fall Time			7.3		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, di/dt=500A/µs		20		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, di/dt=500A/µs		53		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ t≤ 10s and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.
G. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

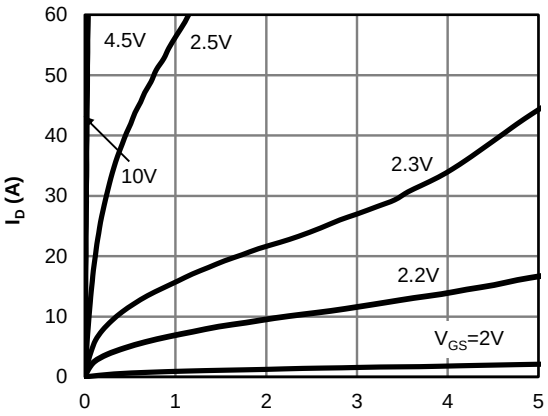


Figure 1: On-Region Characteristics (Note E)

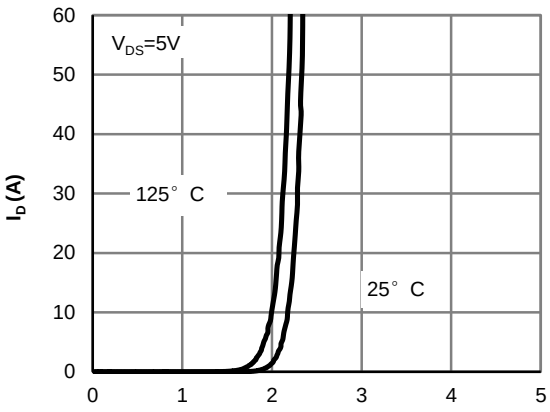


Figure 2: Transfer Characteristics (Note E)

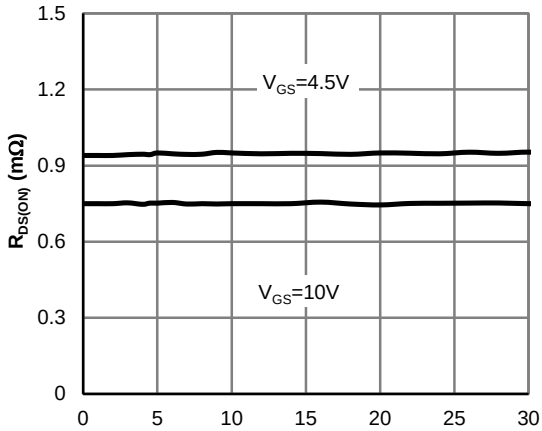


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

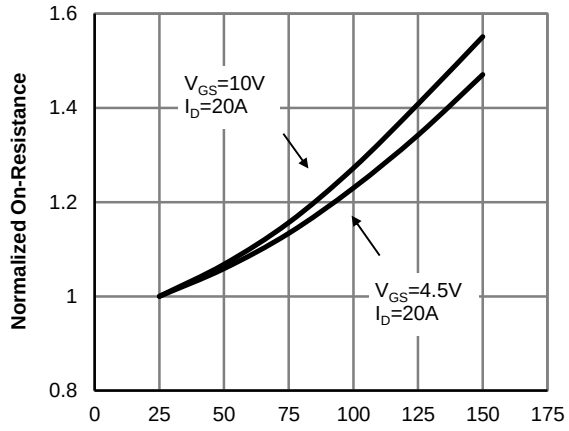


Figure 4: On-Resistance vs. Junction Temperature (Note E)

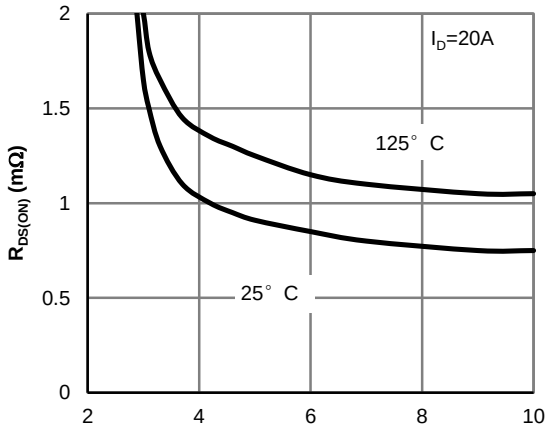


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

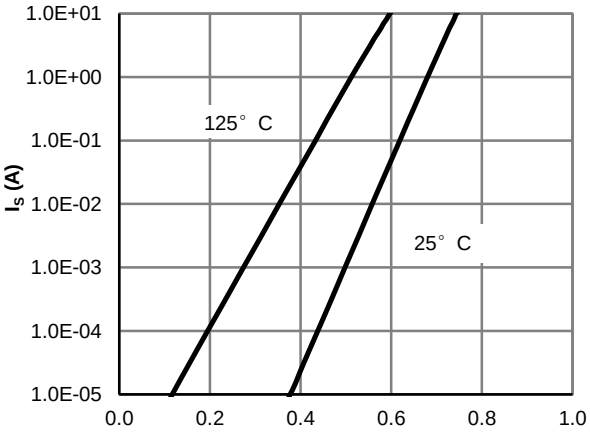


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

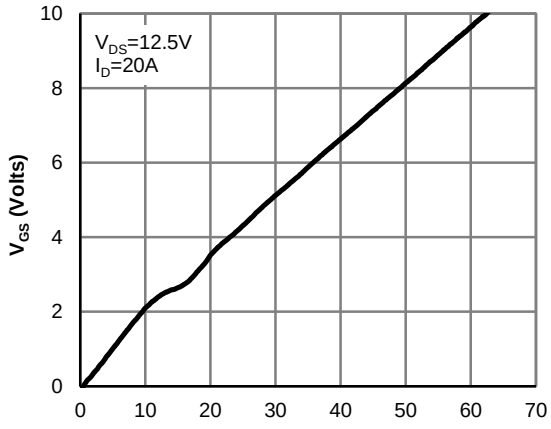


Figure 7: Gate-Charge Characteristics

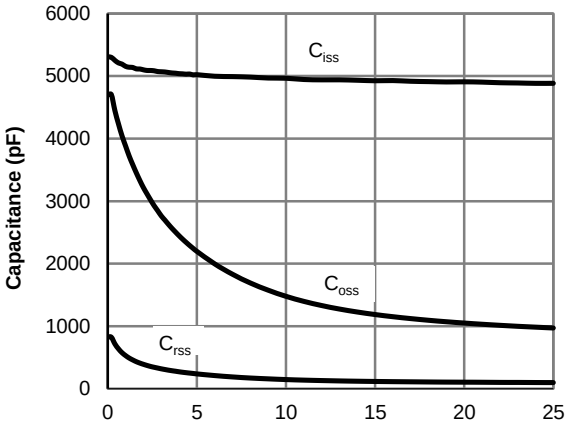


Figure 8: Capacitance Characteristics

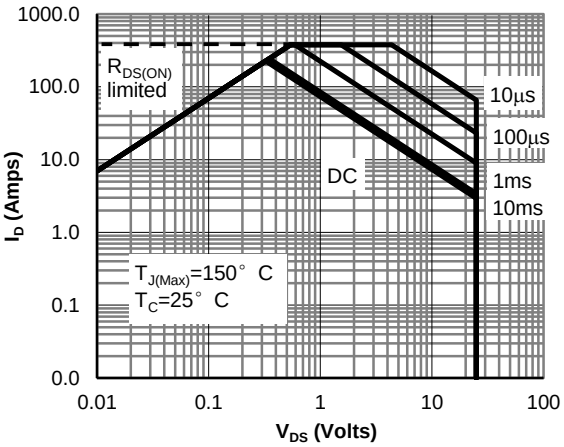


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

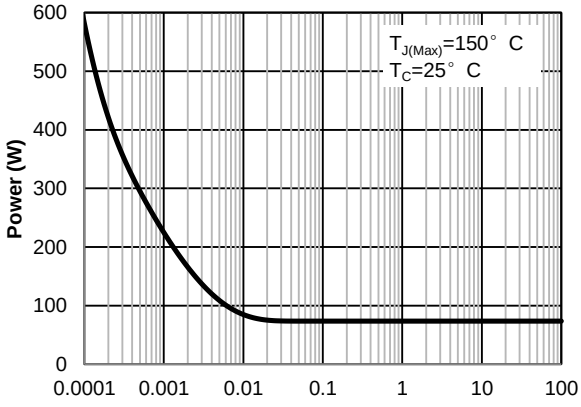


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

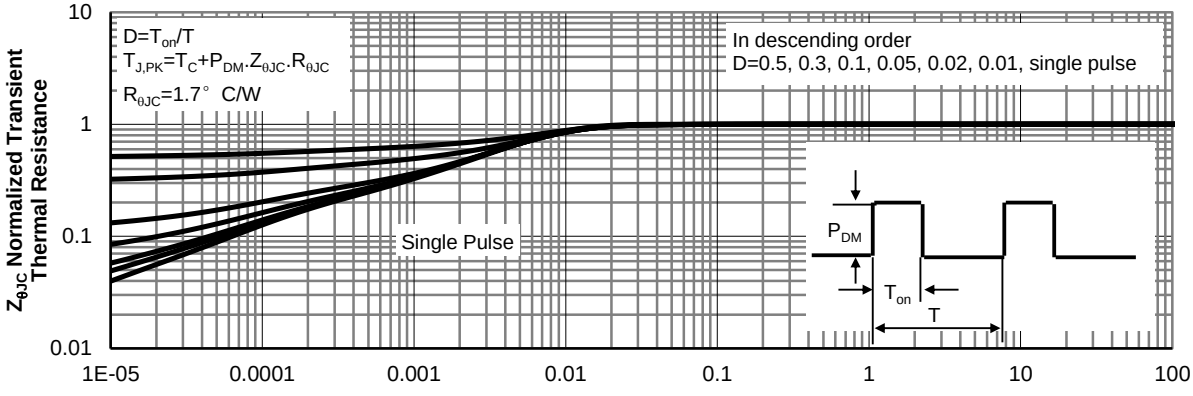


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

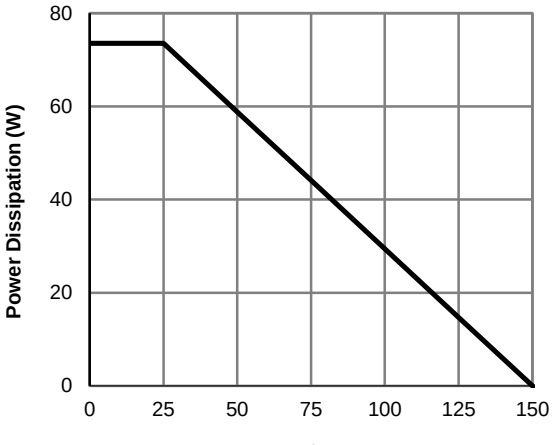


Figure 12: Power De-rating (Note F)

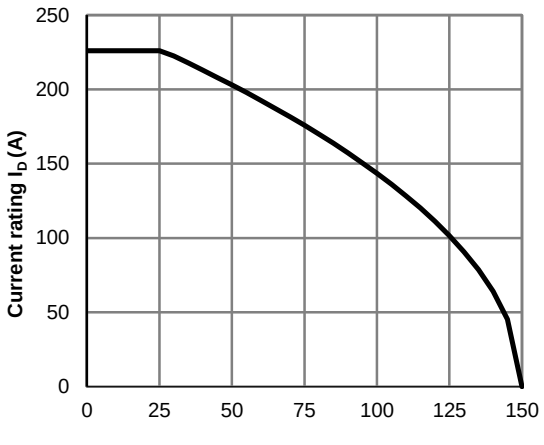


Figure 13: Current De-rating (Note F)

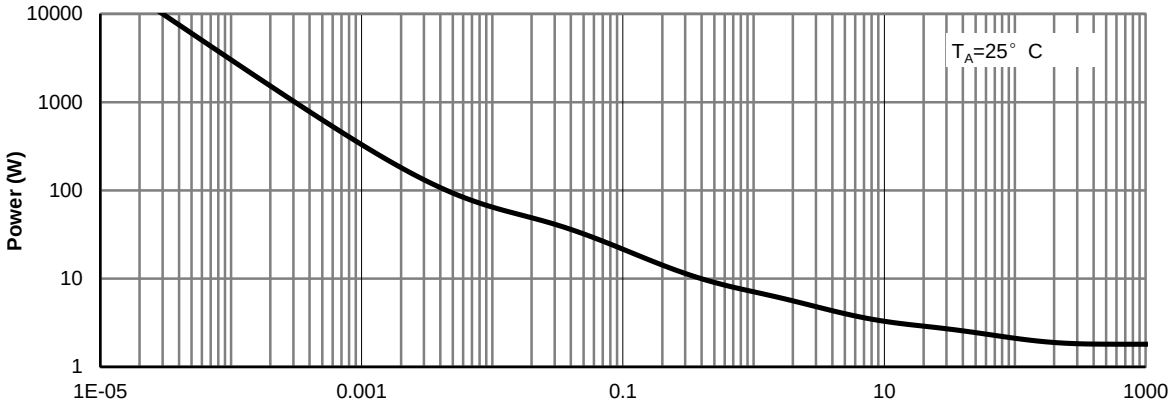


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

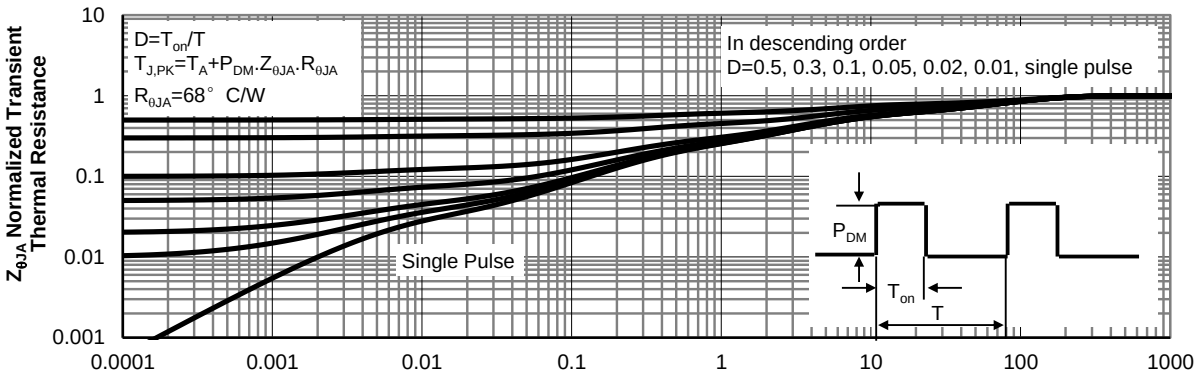


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

Figure A: Gate Charge Test Circuit & Waveforms

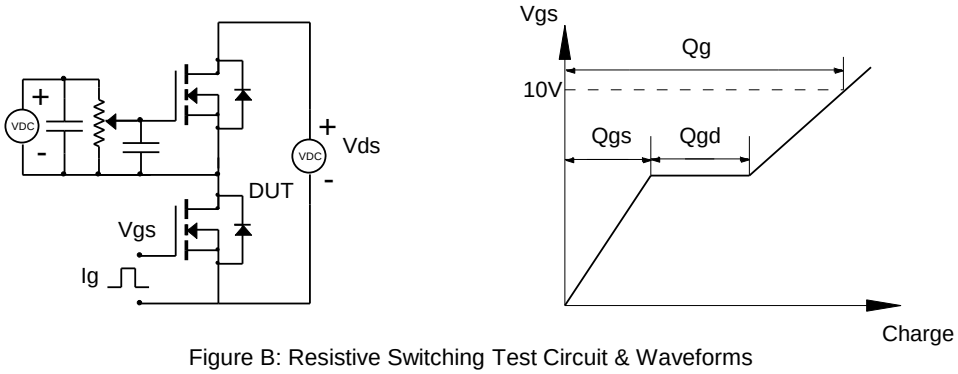


Figure B: Resistive Switching Test Circuit & Waveforms

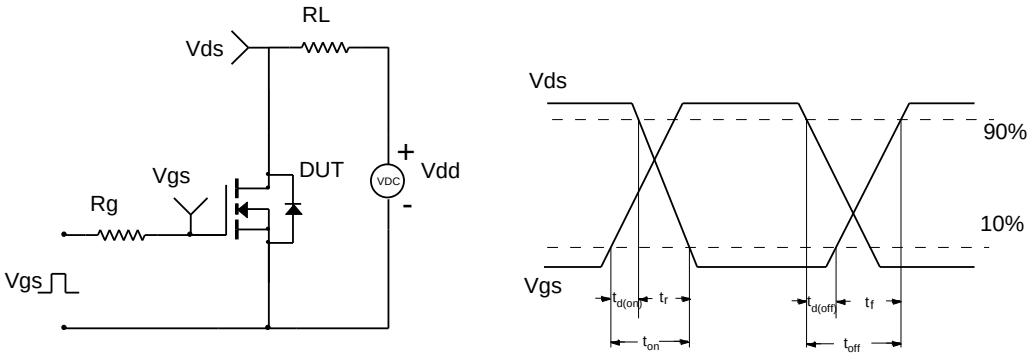


Figure C: Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

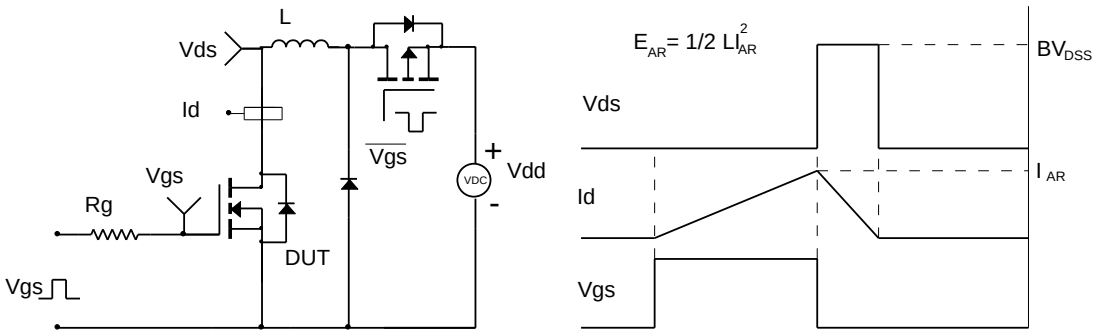


Figure D: Diode Recovery Test Circuit & Waveforms